

Appln No. 09/693,484
Amdt. Dated March 23, 2004
Reply to Office action of December 31, 2003

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Amendments to the Claims:

Amend the claim set, replacing all prior versions, without prejudice or disclaimer of the subject matter thereof, as detailed in the following complete listing of all claims:

1. (Currently amended) A method of manufacturing an integrated circuit carrier (10), the method including the steps of:
providing a substrate (46);
demarcating at least one receiving zone (12) for receiving an integrated circuit or chip (14) on the substrate (46), the integrated circuit electrically associating with a plurality of electrical contacts (42) within the at least one receiving zone, and a plurality of island-defining portions (16) arranged about said at least one receiving zone (12);
forming an electrical terminal (18) on island-defining portions (16), each electrical terminal (18) being electrically connected to one or more of the plurality of electrical contacts (42) within the at least one receiving zone (12); and
creating one or more serpentine members (22) between neighboring island-defining portions (16) by removing material from the substrate (46), thereby reducing thermal strains involving the said island-defining portions (16).
2. (Currently amended) ~~The method of claim 1, which includes forming electrical contacts (42) in said at least one receiving zone (12) and forming an electrical terminal (18) in each island-defining portion (16), each electrical terminal (18) being electrically connected via a track (52) of a circuitry layer (48) to one of the electrical contacts (42).~~
3. (Previously presented) The method of claim 2 which includes forming the circuitry layer (48) on a surface of the substrate (46) by depositing a metal layer on the substrate (46).
4. (Cancelled)
5. (Cancelled)
6. (Previously presented) The method of claim 1 which includes creating the one or more serpentine members (22) by etching through the substrate (46).

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7. (Previously presented) The method of claim 1 which includes forming the substrate (46) from a wafer of undoped silicon having an insulating layer (54).

8. (Previously presented) The method of claim 1 which includes demarcating said at least one receiving zone (12) by forming a recess in the substrate (46).

9. (Previously presented) The method of claim 8 which includes forming the recess by etching the substrate (46).

10. (Cancelled)

11. (Cancelled)